

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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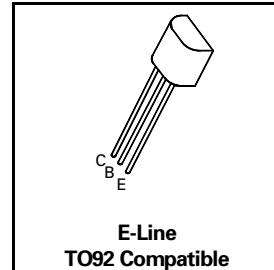
# PNP SILICON PLANAR MEDIUM POWER HIGH VOLTAGE TRANSISTOR

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## FEATURES

- \* 200 Volt  $V_{CEO}$
- \* 1 Amp continuous current
- \*  $P_{tot} = 1$  Watt

**ZTX576**



## ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	$V_{CBO}$	-200	V
Collector-Emitter Voltage	$V_{CEO}$	-200	V
Emitter-Base Voltage	$V_{EBO}$	-5	V
Peak Pulse Current	$I_{CM}$	-2	A
Continuous Collector Current	$I_C$	-1	A
Power Dissipation at $T_{amb}=25^\circ C$	$P_{tot}$	1	W
Operating and Storage Temperature Range	$T_j:T_{stg}$	-55 to +200	°C

## ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^\circ C$ ).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-200			V	$I_C = -100\mu A$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-200			V	$I_C = -10mA^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5			V	$I_E = -100\mu A$
Collector Cut-Off Current	$I_{CBO}$			-0.1	$\mu A$	$V_{CB} = -160V$
Emitter Cut-Off Current	$I_{EBO}$			-0.1	$\mu A$	$V_{EB} = -4V$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			-0.3	V	$I_C = -100mA, I_B = -10mA^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			-1	V	$I_C = -100mA, I_B = -10mA^*$
Base-Emitter Turn-on Voltage	$V_{BE(on)}$			-1	V	$I_C = -100mA, V_{CE} = -10V^*$
Static Forward Current Transfer Ratio	$h_{FE}$	50 50		300		$I_C = -10mA, V_{CE} = -10V^*$ $I_C = -300mA, V_{CE} = -10V^*$
Transition Frequency	$f_T$	100			MHz	$I_C = -50mA, V_{CE} = -10V$ $f = 100MHz$

\*Measured under pulsed conditions. Pulse width=300μs. Duty cycle ≤ 2%

## TYPICAL CHARACTERISTICS

